**R16** 

# Code No: 133AB

# JAWAHARLAL NEHRU TECHNOLOGICAL UNIVERSITY HYDERABAD B.Tech II Year I Semester Examinations, April/May - 2018 ANALOG ELECTRONICS

(Electronics and Communication Engineering)

Time: 3 Hours Max. Marks: 75

**Note:** This question paper contains two parts A and B.

Part A is compulsory which carries 25 marks. Answer all questions in Part A.

Part B consists of 5 Units. Answer any one full question from each unit.

Each question carries 10 marks and may have a, b, c as sub questions.

### PART-A

		<b>(25 Marks)</b>
1.a)	Write the characteristic of CE amplifier.	[2]
b)	Discuss the need of Darlington pair circuit.	[3]
c)	What is meant by gain bandwidth product?	[2]
d)	Short circuit CE current gain of a transistor is 25 at a frequency of 2 MHz. if	$f_{\beta}=200 \text{ kHz}$
	calculate $f_T$ , $h_{fe}$ and $ A_i $ at frequency of 10 MHz and 100 MHz.	[3]
e)	State the advantages and disadvantages of cascode stage.	[2]
f)	What is the folded cascode amplifier? Discuss.	[3]
g)	Classify the various negative feedback amplifers.	[2]
h)	For a phase shift oscillator, the feedback network uses R=6 K $\Omega$ and C=1500 pF. The	
	transistorized amplifier used, has a collector resistance of 18 K $\Omega$ . Calculate t	he frequency
	of oscillation and minimum value of h <sub>fe</sub> of the transistor.	[3]
i)	What is the use of the heat sink in power amplifiers?	[2]
j)	What is meant by loaded and unloaded Q.	[3]
	PART-B	
		(FO N ( . 1 . )

**(50 Marks)** 

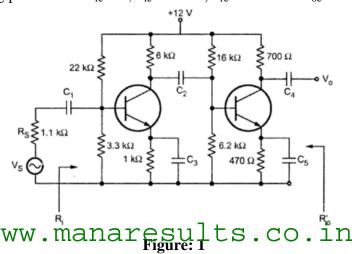
2.a) Discuss the low frequency response of BJT amplifier and the effect of coupling and bypass capacitors.

b) Explain the different coupling schemes used in amplifiers.

[5+5]

#### OR

3. For a two stage amplifier shown in figure 1 calculate (a)Av (b) Avs, (c) Ri (d) Ro Neglect the effect of all capacitances, Assume hat the both the transistors are identical with following parameters.  $h_{fe}=50$ ,  $h_{ie}=1.1$ K $\Omega$ ,  $h_{re}=2.5\times10^{-4}$   $h_{oe}=24\times10^{-6}$  A/V. [10]



- 4.a) For a single stage CE amplifier whose hybrid Π parameters are given below. What value of Rs will give 3 dB frequency  $f_{H'}$  which is half the value obtained with  $R_s$ =0. Hybrid 'Π' parameters are:  $g_m$ =50 mA/V,  $r_{bb}$ =100Ω,  $r_{b'e}$ =1 K ,  $C_C$ =3 pF,  $C_e$ =100 pF.
  - b) A BJT has the following parameters measured at  $I_c$ =1 mA,  $h_{ie}$ =3 K  $\Omega$ ,  $h_{fe}$ =100,  $f_T$ =4 MHz,  $C_C$ =2pF and  $C_e$ =18 pF. Find  $r_{b'e}$ ,  $r_{bb'}$ ,  $g_m$  and  $f_H$  for  $R_L$ =1 K $\Omega$ . [5+5]

OR

- 5.a) Prove that  $h_{fe}=g_m r_{b'e}$ .
  - b) Derive the expression for CE short circuit current gain A<sub>i</sub> as a function of frequency.

[4+6]

- 6.a) Compare the performance of BJT and FET amplifiers.
  - b) Draw and explain the CS amplifier with current source load. Derive an expression for  $A_{v.}$  [5+5]

OR

- 7.a) Draw and explain the MOS small signal model.
  - b) Discuss the analysis of CD JFET amplifier.

[5+5]

- 8.a) What are the advantages and disadvantages of negative amplifier in detail?
  - b) For the given circuit shown in figure 2, calculate  $R_{mf}$ ,  $A_{vf}$  and  $R_{if}$ . The transistors with parameters  $h_{ie}=2$  K,  $h_{fe}=100$ . Neglect  $h_{oe}$  and  $h_{re}$ . [5+5]

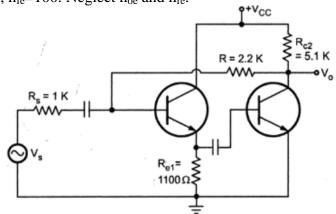


Figure: 2 OR

- 9.a) In a colpitt's oscillator, the values of the inductors and capacitors in the tank circuit are L=40 mH,  $C_1=100 \text{ pF}$ ,  $C_2=500 \text{ pF}$ .
  - i)Find the frequency of oscillation.
  - ii) if the output voltage is 10 V, find the feedback voltage.
  - iii) find the minimum gain, if the frequency is changed by changing 'L' alone.
  - iv)find the value of  $c_1$ , for a gain of 10.
  - v)also find the new frequency of oscillation.
  - b) Compare the RC phase shift and wein bridge oscillators.

[5+5]

- 10.a) Explain the principle of operation of class C amplifier.
  - b) Design a class B power amplifier to deliver 25 W to a load resistors  $R_L$ =8  $\Omega$  using transformer coupling,  $V_m$ = $V_{CC}$ =25 V. Assume reasonable data where ever necessary.

[5+5]

# OR

- 11.a) An RF tuned voltage amplifier using FET with  $r_d$ =100 K $\Omega$  and  $g_m$ =500 $\mu$ s has tuned circuit, consisting of L=2.5mH and C=200 pF as its load. At its resonant frequency, the circuit offers an equivalent shunt resistance of 100 K $\Omega$ . For the amplifier, determine the (i) the resonant gain (ii) the effective Q and (iii) the bandwidth.
  - b) Draw and explain the double tuned amplifier with the help of the frequency response.

[5+5]

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